



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

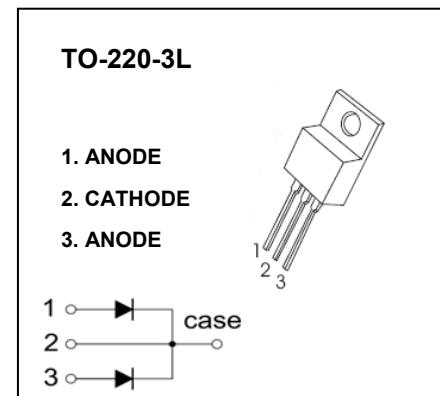
## TO-220-3L Plastic-Encapsulate Diodes

### SBL1030CT, 35CT, 40CT, 45CT, 50CT, 60CT

SCHOTTKY BARRIER RECTIFIER

#### FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



#### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted )

Symbol	Parameter	Value						Unit
		SBL 1030CT	SBL 1035CT	SBL 1040CT	SBL 1045CT	SBL 1050CT	SBL 1060CT	
$V_{RRM}$	Peak repetitive reverse voltage							
$V_{RWM}$	Working peak reverse voltage	30	35	40	45	50	60	V
$V_R$	DC blocking voltage							
$V_{R(RMS)}$	RMS reverse voltage	21	24.5	28	31.5	35	42	V
$I_o$	Average rectified output current@ $T_c=95^\circ\text{C}$				10			A
$I_{FSM}$	Non-Repetitive peak forward surge current 8.3ms half sine wave				175			A
$P_D$	Power dissipation				2			W
$R_{QJA}$	Thermal resistance from junction to ambient				50			$^\circ\text{C/W}$
$T_j$	Junction temperature				125			$^\circ\text{C}$
$T_{stg}$	Storage temperature				-55~+150			$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Device	Test conditions	Min	Typ	Max	Unit
<b>Reverse voltage</b>	$V_{(\text{BR})}$	SBL1030CT	$I_R=0.5\text{mA}$	30			V
		SBL1035CT		35			
		SBL1040CT		40			
		SBL1045CT		45			
		SBL1050CT		50			
		SBL1060CT		60			
<b>Reverse current</b>	$I_R$	SBL1030CT	$V_R=30\text{V}$			0.5	mA
		SBL1035CT	$V_R=35\text{V}$				
		SBL1040CT	$V_R=40\text{V}$				
		SBL1045CT	$V_R=45\text{V}$				
		SBL1050CT	$V_R=50\text{V}$				
		SBL1060CT	$V_R=60\text{V}$				
<b>Forward voltage</b>	$V_F$	SBL1030CT-1045CT	$I_F=5\text{A}$			0.55	V
		SBL1050CT,1060CT				0.7	
<b>Typical total capacitance</b>	$C_{\text{tot}}$	SBL1030CT-1060CT	$V_R=4\text{V}, f=1\text{MHz}$		450		pF